AMORPHOUS GE/TE DEPOSITION PROCESS

ABSTRACT

Germanium, tellurium, and/or antimony precursors are usefully employed to form germanium-, tellurium- and/or antimony-containing films, such as films of GeTe, GST, and thermoelectric germanium-containing films. Processes for using these precursors to form amorphous films are also described. Further described is the use of $[\{nBuC(iPrN)_2\}_2Ge]$ or Ge butyl amidinate to form GeTe smooth amorphous films for phase change memory applications.

Figure 13